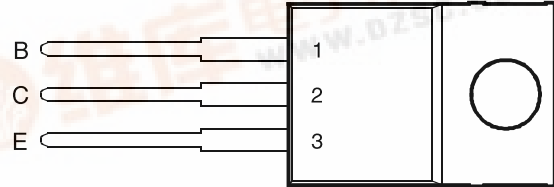




## BDX54, BDX54A, BDX54B, BDX54C PNP SILICON POWER DARLINGTONS

- Designed for Complementary Use with BDX53, BDX53A, BDX53B and BDX53C
- 60 W at 25°C Case Temperature
- 8 A Continuous Collector Current
- Minimum  $h_{FE}$  of 750 at 3 V, 3 A

TO-220 PACKAGE  
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ( $I_E = 0$ )	BDX54	$V_{CBO}$	-45	V
	BDX54A		-60	
	BDX54B		-80	
	BDX54C		-100	
Collector-emitter voltage ( $I_B = 0$ )	BDX54	$V_{CEO}$	-45	V
	BDX54A		-60	
	BDX54B		-80	
	BDX54C		-100	
Emitter-base voltage		$V_{EBO}$	-5	V
Continuous collector current		$I_C$	-8	A
Continuous base current		$I_B$	-0.2	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 1)		$P_{tot}$	60	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 2)		$P_{tot}$	2	W
Operating junction temperature range		$T_j$	-65 to +150	°C
Operating temperature range		$T_{stg}$	-65 to +150	°C
Operating free-air temperature range		$T_A$	-65 to +150	°C

NOTES: 1. Derate linearly to 150°C case temperature at the rate of 0.48 W/°C.  
2. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

# BDX54, BDX54A, BDX54B, BDX54C PNP SILICON POWER DARLINGTONS

## electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -100 \text{ mA}$	$I_B = 0$	(see Note 3)	BDX54 BDX54A BDX54B BDX54C	-45 -60 -80 -100		V
$I_{CEO}$	Collector-emitter cut-off current	$V_{CE} = -30 \text{ V}$ $V_{CE} = -30 \text{ V}$ $V_{CE} = -40 \text{ V}$ $V_{CE} = -50 \text{ V}$	$I_B = 0$ $I_B = 0$ $I_B = 0$ $I_B = 0$		BDX54 BDX54A BDX54B BDX54C		-0.5 -0.5 -0.5 -0.5	mA
$I_{CBO}$	Collector cut-off current	$V_{CB} = -45 \text{ V}$ $V_{CB} = -60 \text{ V}$ $V_{CB} = -80 \text{ V}$ $V_{CB} = -100 \text{ V}$	$I_E = 0$ $I_E = 0$ $I_E = 0$ $I_E = 0$		BDX54 BDX54A BDX54B BDX54C		-0.2 -0.2 -0.2 -0.2	mA
$I_{EBO}$	Emitter cut-off current	$V_{EB} = -5 \text{ V}$	$I_C = 0$				-2	mA
$h_{FE}$	Forward current transfer ratio	$V_{CE} = -3 \text{ V}$	$I_C = -3 \text{ A}$	(see Notes 3 and 4)		750		
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_B = -12 \text{ mA}$	$I_C = -3 \text{ A}$	(see Notes 3 and 4)			-2.5	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_B = -12 \text{ mA}$	$I_C = -3 \text{ A}$	(see Notes 3 and 4)			-2	V
$V_{EC}$	Parallel diode forward voltage	$I_E = -3 \text{ A}$	$I_B = 0$				-2.5	V

NOTES: 3. These parameters must be measured using pulse techniques,  $t_p = 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .

4. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

## thermal characteristics

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			2.08	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			62.5	°C/W

## resistive-load-switching characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS †			MIN	TYP	MAX	UNIT
$t_{on}$	Turn-on time	$I_C = -3 \text{ A}$	$I_{B(on)} = -12 \text{ mA}$	$I_{B(off)} = 12 \text{ mA}$		1		$\mu\text{s}$
$t_{off}$	Turn-off time	$V_{BE(off)} = 4.2 \text{ V}$	$R_L = 10 \Omega$	$t_p = 20 \mu\text{s}$ , dc $\leq 2\%$		5		$\mu\text{s}$

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

**BDX54, BDX54A, BDX54B, BDX54C  
PNP SILICON POWER DARLINGTONS**

**TYPICAL CHARACTERISTICS**

**TYPICAL DC CURRENT GAIN  
VS  
COLLECTOR CURRENT**

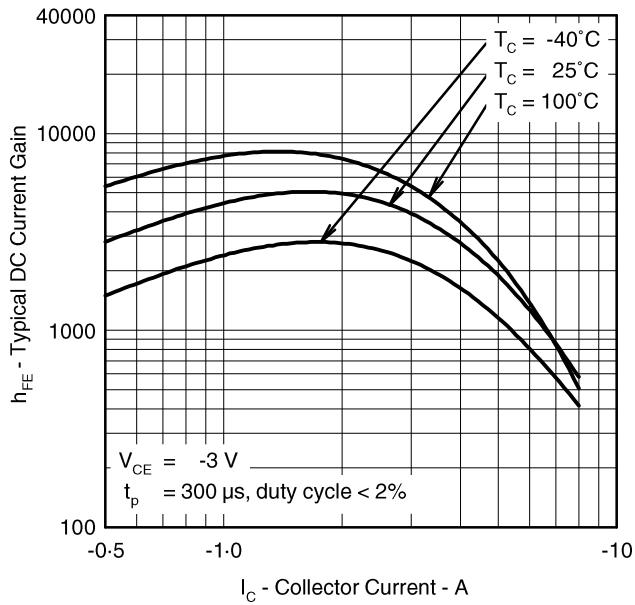


Figure 1.

**COLLECTOR-EMITTER SATURATION VOLTAGE  
VS  
COLLECTOR CURRENT**

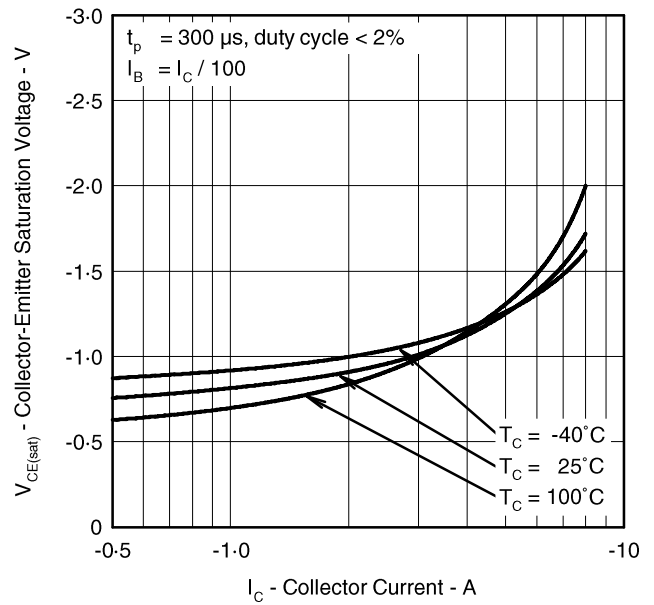


Figure 2.

**BASE-EMITTER SATURATION VOLTAGE  
VS  
COLLECTOR CURRENT**

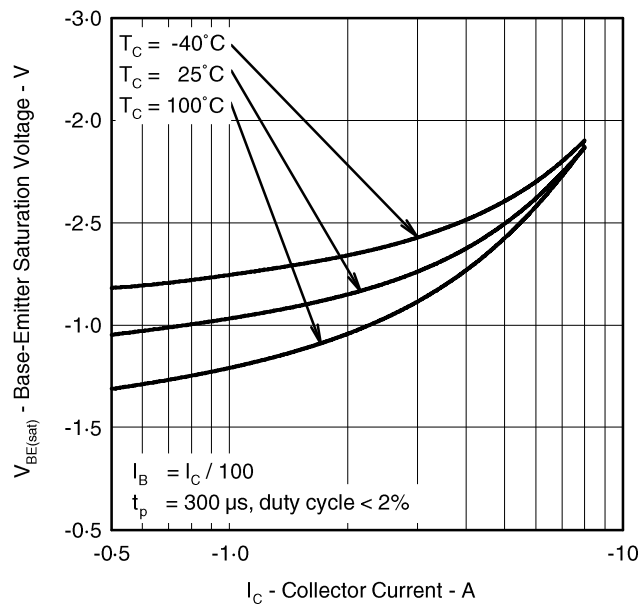


Figure 3.

**BDX54, BDX54A, BDX54B, BDX54C  
PNP SILICON POWER DARLINGTONS**

**MAXIMUM SAFE OPERATING REGIONS**

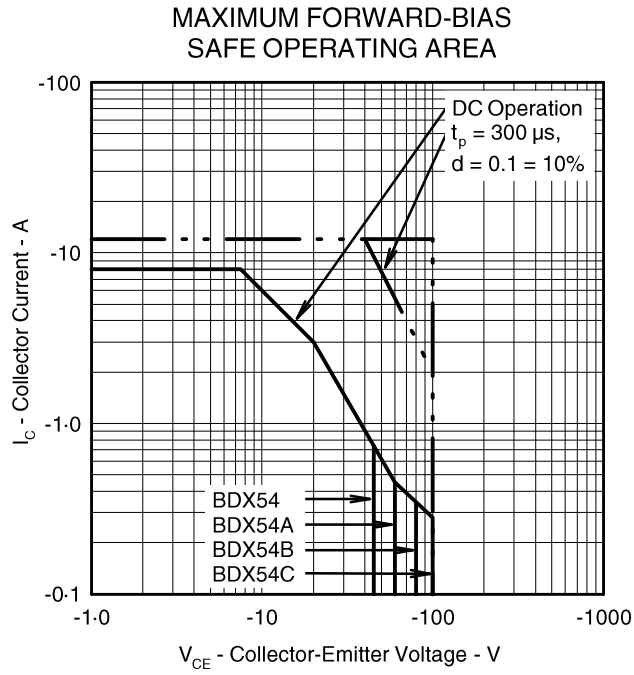


Figure 4.

**THERMAL INFORMATION**

**MAXIMUM POWER DISSIPATION  
vs  
CASE TEMPERATURE**

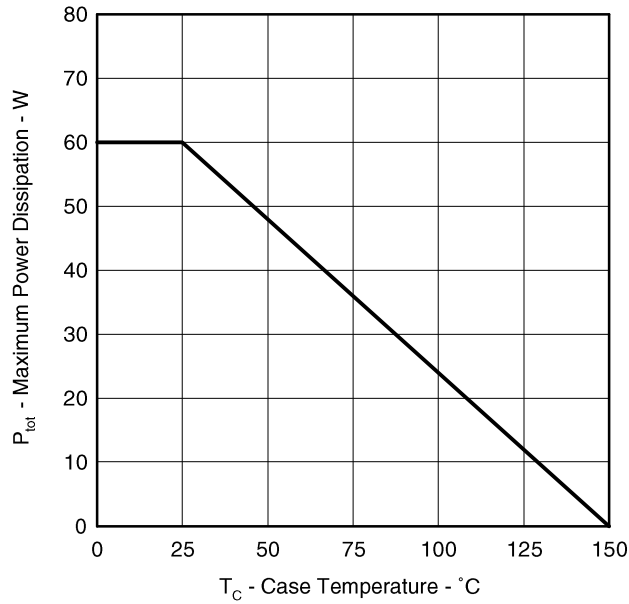


Figure 5.

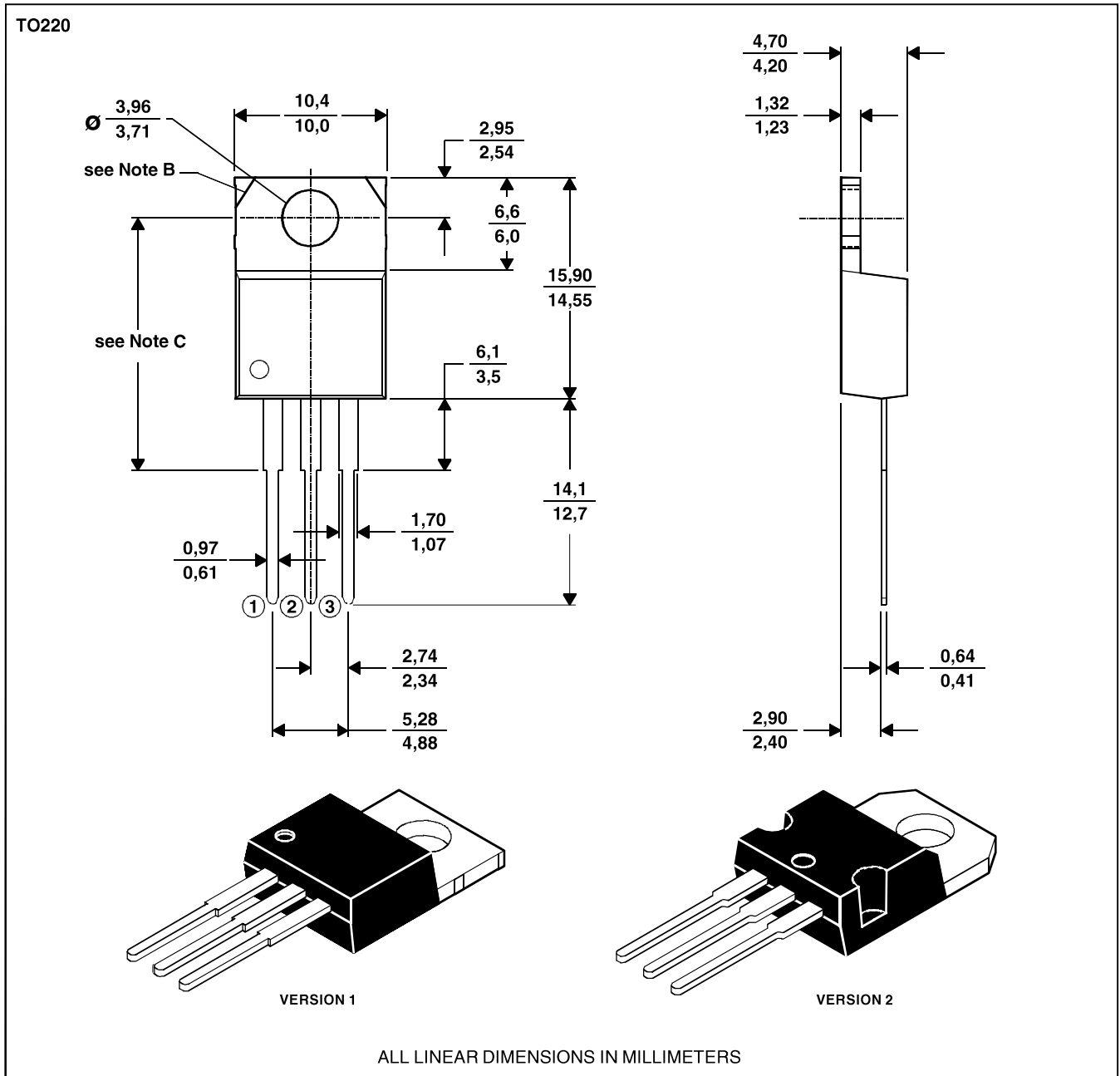
# BDX54, BDX54A, BDX54B, BDX54C PNP SILICON POWER DARLINGTONS

## MECHANICAL DATA

### TO-220

#### 3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



- NOTES: A. The centre pin is in electrical contact with the mounting tab.  
 B. Mounting tab corner profile according to package version.  
 C. Typical fixing hole centre stand off height according to package version.  
 Version 1, 18.0 mm. Version 2, 17.6 mm.